# 2.5V Drive Nch MOS FET

## 2SK3018

### Structure

Silicon N-channel MOSFET

### Applications

Interfacing, switching (30V, 100mA)

#### ●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Low voltage drive (2.5V) makes this device ideal for portable equipment.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.

### Packaging specifications

Туре	Package	Taping
	Code	T106
	Basic ordering unit (pieces)	3000
2SK3018		0

### ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		Voss	30	V
Gate-source voltage		Vgss	±20	V
Drain current	Continuous	lo	±100	mA
Diain current	Pulsed	IDP*1	±400	mA
Total power dissipation		Pp*2	200	mW
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

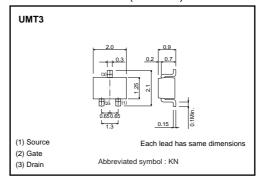
<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

### ●Thermal resistance

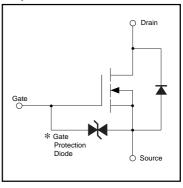
Parameter	Symbol	Limits	Unit	
Channel to ambient	Rth(ch-a) *	625	°C / W	

<sup>\*</sup> With each pin mounted on the recommended lands.

### ●External dimensions (Unit : mm)



### ●Equivalent circuit



\*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use a protection circuit when the fixed voltages are exceeded.

st2 With each pin mounted on the recommended lands.

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	-	±1	μΑ	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	30	_	_	V	ID = 10μA, VGS = 0V
Zero gate voltage drain current	IDSS	-	-	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate threshold voltage	VGS(th)	0.8	_	1.5	V	V <sub>DS</sub> = 3V, I <sub>D</sub> = 100μA
Static drain-source on-state	RDS(on)	_	5	8	Ω	I <sub>D</sub> = 10mA, V <sub>G</sub> s = 4V
resistance	RDS(on)	_	7	13	Ω	ID = 1mA, VGS = 2.5V
Forward transfer admittance	Yfs	20	_	_	mS	V <sub>DS</sub> = 3V, I <sub>D</sub> = 10mA
Input capacitance	Ciss	_	13	_	pF	V <sub>DS</sub> = 5V
Output capacitance	Coss	_	9	_	pF	Vgs = 0V
Reverse transfer capacitance	Crss	_	4	_	pF	f = 1MHz
Turn-on delay time	td(on)	-	15	_	ns	I <sub>D</sub> = 10mA, V <sub>DD</sub> ≒5V
Rise time	tr	_	35	_	ns	Vgs = 5V
Turn-off delay time	td(off)	_	80	_	ns	R <sub>L</sub> = 500Ω
Fall time	tr	_	80	_	ns	$R_G = 10\Omega$

### •Electrical characteristic curves

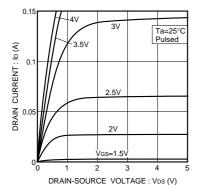


Fig.1 Typical output characteristics

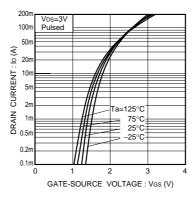


Fig.2 Typical transfer characteristics

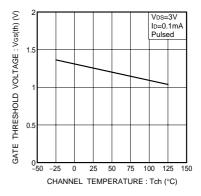


Fig.3 Gate threshold voltage vs. channel temperature

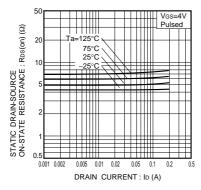


Fig.4 Static drain-source on-state resistance vs. drain current ( I )

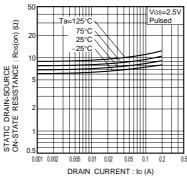


Fig.5 Static drain-source on-state resistance vs. drain current (II)

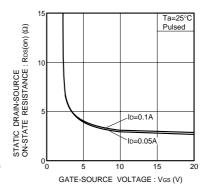


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

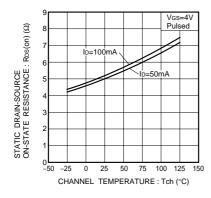


Fig.7 Static drain-source on-state resistance vs. channel temperature

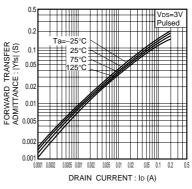


Fig.8 Forward transfer admittance vs. drain current

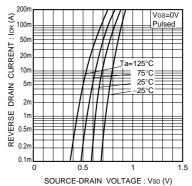


Fig.9 Reverse drain current vs. source-drain voltage ( I )

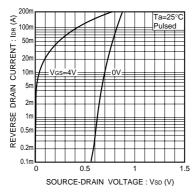


Fig.10 Reverse drain current vs. source-drain voltage (II)

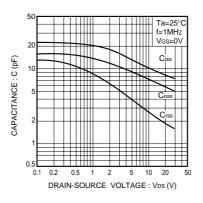


Fig.11 Typical capacitance vs. drain-source voltage

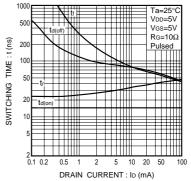


Fig.12 Switching characteristics (See Figures 13 and 14 for the measurement circuit and resultant waveforms)

### •Switching characteristics measurement circuit

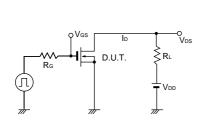


Fig.13 Switching time measurement circuit

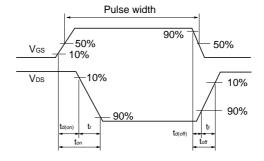


Fig.14 Switching time waveforms

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